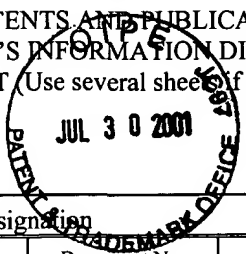






















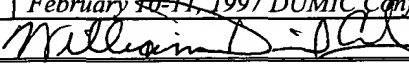


FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Attorney Docket No.: A5771/T42200		Application No.: 09/854,083		
		Applicant: ZHENGQUAN TAN et al.				
		Filing Date: May 11, 2001		Group: <del>Unassigned</del> 2823		
Reference Designation <span style="float: right;">Page 1</span>						
<b>U.S. PATENT DOCUMENTS</b>						
Examiner Initial	Document No.	Date	Name	Class	Sub-class	Filing Date (If Appropriate)
 AA	4,667,365	05/26/87	Martinek	16	35 D	
 AB	4,894,352	01/16/90	Lane et al.	437	238	
 AC	5,013,691	05/07/91	Lory et al.	437	238	
 AD	5,571,571	11/05/96	Musaka et al.	427	574	
 AE	5,571,576	11/05/96	Qian et al.	427	574	
 AF	5,728,621	03/17/98	Zheng et al.	438	427	
 AG	5,750,211	05/12/98	Weise et al.	427	579	
 AH	5,872,058	02/16/99	Van Cleemput et al.	438	692	
 AI	6,020,458	02/01/00	Lee et al.	528	401	
 AJ	6,051,321	04/18/00	Lee et al.	428	447	
 AK	6,149,779	11/21/00	Van Cleemput	204	192.37	
 AL	6,150,212	11/21/00	Divakaruni et al.	438	244	
 AM	6,150,285	11/21/00	Besser et al.	438	787	
 AN	6,194,038	02/27/01	Rossman	427	569	
 AO	6,197,691	03/06/01	Lee	438	691	
<b>FOREIGN PATENT DOCUMENTS</b>						
	Document No.	Date	Country	Class	Sub-class	Translation (Yes/No)
 AP	EP 0 822 585 A2	02/04/98	Europe	H01L	21/316	yes
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>						
 AQ	V.Y. Vassiliev et al., "Trends in Void Free Pre-metal CVD Dielectrics," <i>Solid State Technology</i> , pp. 129-136 (March 2001).					
 AR	L.Q. Qian et al., "High Density Plasma Deposition and Deep Submicron Gap Fill with Low Dielectric Constant SiOF Films," <i>February 21-22, 1995 DUMIC Conference</i> , pp. 50-56 (February 1995).					
 AS	T. Fukada et al., "Preparation of SiOF with Low Dielectric Constant by ECR Plasma CVD," <i>February 21-22, 1995 DUMIC Conference</i> , pp. 43-49 (February 1995).					
 AT	D. Yu et al., "Step Coverage Study of PETEOS Deposition for Intermetal Dielectric Applications," <i>June 12-13, 1990 VMIC Conference</i> , pp. 166-172 (June 1990).					
 AU	K. Musaka et al., "Single Step Gap Filling Technology for Subhalf Micron Metal Spacings on Plasma Enhanced TEOS/O <sub>2</sub> Chemical Vapor Deposition System," <i>Extended Abstracts of the 1993 International Conference on Solid State Devices and Materials, Makuhari</i> , pp. 510-512 (1993).					
 AV	T. Fukuda et al., "Highly Reliable SiOF Film Formation Using High Density Plasma Containing Hydrogen," <i>February 10-11, 1997 DUMIC Conference</i> , pp. 41-49 (February 1997).					
EXAMINER  DATE CONSIDERED <u>April 12, 2002</u>						

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.